# Refine Search

#### Search Results -

Terms	Documents
L6 and (lightly near2 doped)	13

US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database

Derwent World Patents Index
| IBM Technical Disclosure Bulletins

Search:

Database:

Refine Search

Recall Text 🗢

Clear

Interrupt

### Search History

DATE: Sunday, March 21, 2004 Printable Copy Create Case

Set Name Query side by side		Hit Count Set Name result set	
DB=U	SPT; PLUR=YES; OP=ADJ		
<u>L7</u>	L6 and (lightly near2 doped)	13	<u>1.7</u>
<u>L6</u>	L5 and (high adj voltage)	13	<u>L6</u>
<u>L5</u>	L3 and polysilicon and (silicide or salicide)	18	<u>L5</u>
<u>I.4</u>	L3 and polysilicon and saliciding	0	<u>L4</u>
<u>L3</u>	L2 and (high adj K)	21	<u>1.3</u>
<u>L2</u>	L1 and IMD	197	<u>L2</u>
<u>L1</u>	gate near2 electrodes	49881	<u>L.1</u>

END OF SEARCH HISTORY

## **Hit List**

Generate Collection Fwd Refs Clear Print Bkwd Refs Generate OACS

Search Results - Record(s) 1 through 10 of 13 returned.

1. Document ID: US 6686236 B2

L7: Entry 1 of 13

File: USPT

Feb 3, 2004

oct 21, 2003

US-PAT-NO: 6686236

DOCUMENT-IDENTIFIER: US 6686236 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference Claims KMC Draw Do 2. Document ID: US 6635528 B2 Oct 21, 2003

File: USPT

US-PAT-NO: 6635528

L7: Entry 2 of 13

DOCUMENT-IDENTIFIER: US 6635528 B2

\*\* See image for Certificate of Correction \*\*

TITLE: Method of planarizing a conductive plug situated under a ferroelectric

capacitor

Claims KWMC Draw De Full Title Citation Front Review Classification Date Reference 3. Document ID: US 6635498 B2 L7: Entry 3 of 13 File: USPT Oct 21, 2003

US-PAT-NO: 6635498

DOCUMENT-IDENTIFIER: US 6635498 B2

L7: Entry 4 of 13

TITLE: Method of patterning a FeRAM capacitor with a sidewall during bottom

electrode etch

Full Title Citation Front Review Classification Date Reference Claims KNNC Draw. Do 4. Document ID: US 6635497 B2

File: USPT

Page 2 of 3 Record List Display

US-PAT-NO: 6635497

DOCUMENT-IDENTIFIER: US 6635497 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic

chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference GIEIMS KUG DIEW De

5. Document ID: US 6596547 B2

L7: Entry 5 of 13

File: USPT

Jul 22, 2003

US-PAT-NO: 6596547

DOCUMENT-IDENTIFIER: US 6596547 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference Claims KWC Draw De 6. Document ID: US 6576546 B2

L7: Entry 6 of 13

File: USPT

Jun 10, 2003

US-PAT-NO: 6576546

DOCUMENT-IDENTIFIER: US 6576546 B2

TITLE: Method of enhancing adhesion of a conductive barrier layer to an underlying conductive plug and contact for ferroelectric applications

Full Title Citation Front Review Classification Date Reference: Claims Killic Draw De

7. Document ID: US 6548343 B1

L7: Entry 7 of 13

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

Full Title Citation Front Review Classification Date Reference Classification Date Reference

8. Document ID: US 6534809 B2

L7: Entry 8 of 13

File: USPT

Mar 18, 2003

US-PAT-NO: 6534809

DOCUMENT-IDENTIFIER: US 6534809 B2

\*\* See image for Certificate of Correction \*\*

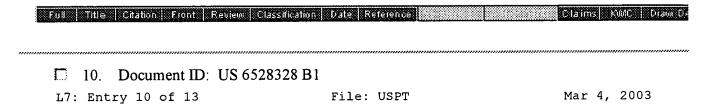
TITLE: Hardmask designs for dry etching FeRAM capacitor stacks

Full Title Citation Front Revie	on Classification Date Reference	Claims KMC Draw D
·····		
9. Document ID: US	6528386 B1	
L7: Entry 9 of 13	File: USPT	Mar 4, 2003

US-PAT-NO: 6528386

DOCUMENT-IDENTIFIER: US 6528386 B1

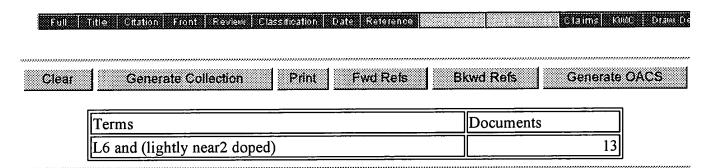
TITLE: Protection of tungsten alignment mark for FeRAM processing



US-PAT-NO: 6528328

DOCUMENT-IDENTIFIER: US 6528328 B1

TITLE: Methods of preventing reduction of irox during PZT formation by metalorganic chemical vapor deposition or other processing



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# **Hit List**

Generate Collection Print Fwd Refs **Bkwd Refs** Clear Generate OACS

Search Results - Record(s) 11 through 13 of 13 returned.

11. Document ID: US 6500678 B1

L7: Entry 11 of 13

File: USPT

Dec 31, 2002

US-PAT-NO: 6500678

DOCUMENT-IDENTIFIER: US 6500678 B1

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference Claims KMC Draw De 12. Document ID: US 6492222 B1 Dec 10, 2002

File: USPT

US-PAT-NO: 6492222

DOCUMENT-IDENTIFIER: US 6492222 B1

L7: Entry 12 of 13

TITLE: Method of dry etching PZT capacitor stack to form high-density ferroelectric

memory devices

Claims KWIC Draw Da Full Title Chatton Front Review Classification Date Reference

13. Document ID: US 6485988 B2

L7: Entry 13 of 13

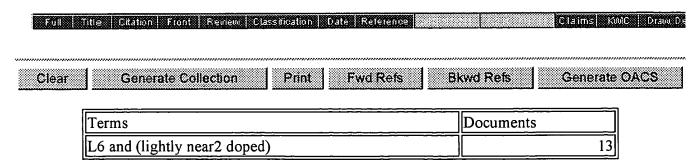
File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation



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